



High Voltage Fast Switching PNP Power Transistor

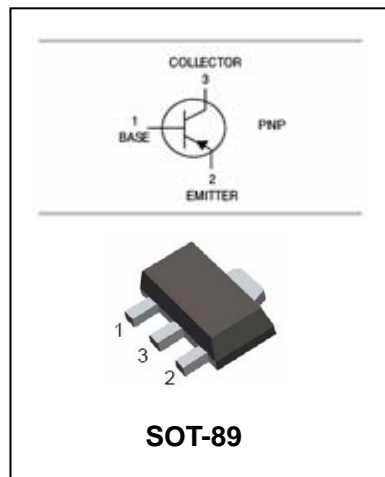
3CD14002

FEATURES

- $P_C=1W$ (Mounted on ceramic substrate).
- High speed switching.
- Small flat package.



Lead-free



APPLICATIONS

- High voltage switch mode application.

ORDERING INFORMATION

Type No.	Marking	Package Code
3CD14002	14002	SOT-89

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-400	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-1	A
P_C	Collector Dissipation	1.25	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -400V, I_E = 0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-100	μA
DC current gain	h_{FE}	$V_{CE} = -10V, I_C = -200mA$	9		40	
		$V_{CE} = -10V, I_C = -250\mu A$	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -200mA, I_B = -40mA$			-0.8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -200mA, I_B = -40mA$			-1.1	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -100mA,$ $f = 1MHz$	5			MHz
Fall time	t_f	$I_C = 1A, I_{B1} = I_{B2} = 0.2A,$ $V_{CC} = 100V$			0.5	μS
Storage time	t_s				2.5	μS

CLASSIFICATION OF $h_{FE(1)}$

Range	9-15	15-20	20-25	25-30	30-35	35-40

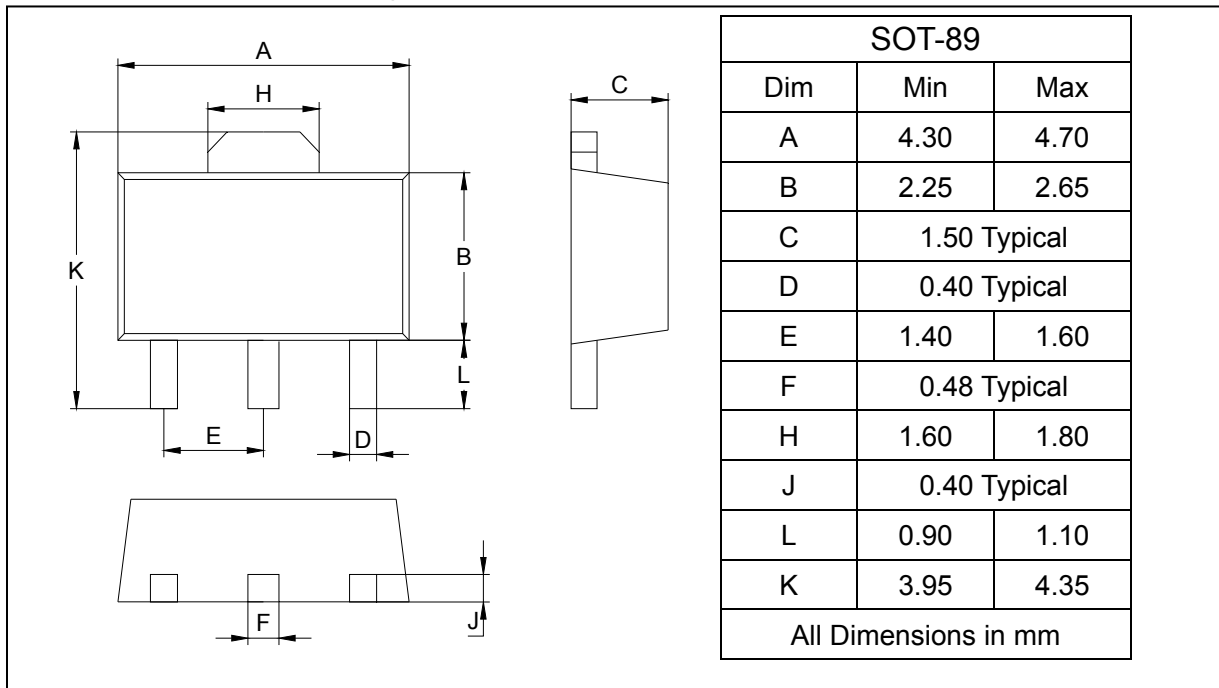
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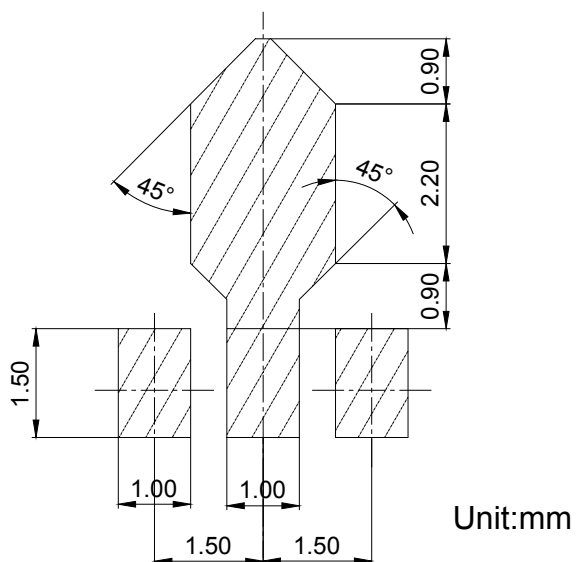
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
3CD14002	SOT-89	1000/Tape&Reel